

N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

29 January 2019

Product data sheet

1. General description

Automotive qualified logic level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
- · Low power losses, high power density
- LFPAK copper clip package technology:
 - High robustness and reliability
 - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

3. Applications

- 12 V automotive systems
- · Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	30	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	44	W
Static char	acteristics	·		·			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11		8.4	12.1	15	mΩ
Dynamic cl	haracteristics				_		
Q _{GD}	gate-drain charge	I_D = 10 A; V_{DS} = 20 V; V_{GS} = 4.5 V; Fig. 13; Fig. 14		-	1.2	2.5	nC
Source-dra	in diode	·		·			
Q _r	recovered charge	I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 20 V		-	11	-	nC

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N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S		$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 17}$	-	0.57	-	

[1] 30A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D.
2	S	source		
3	S	source		G (T
4	G	gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information							
Type number	mber Package						
	Name	Description	Version				
BUK9M15-40H	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

7. Marking

Table 4. Marking codes			
Type number	Marking code		
BUK9M15-40H	91540H		

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	16	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	44	W
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	30	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	27.4	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	155	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					

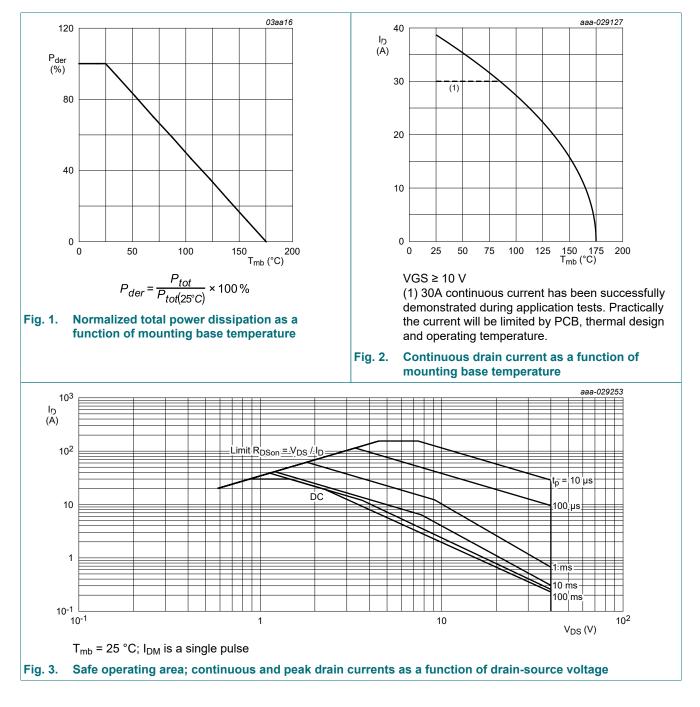
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Symbol	Parameter	Conditions		Min	Max	Unit
I _S	source current	T _{mb} = 25 °C		-	30	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	155	А
Avalanche rugg	edness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ I_D = 30 \text{ A}; \text{V}_{\text{sup}} \leq 40 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} = 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} $	[2] [3]	-	10.7	mJ

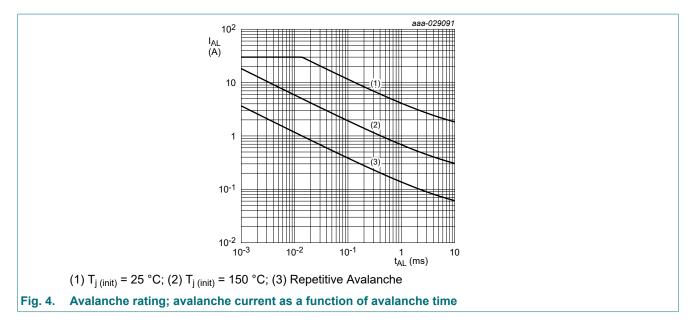
[1] 30A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

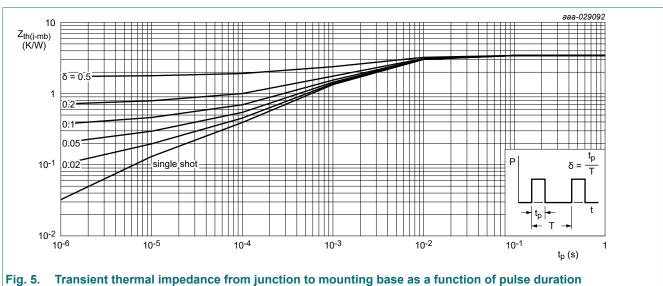


N-channel 40 V, 15.0 mΩ logic level MOSFET in LFPAK33



9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	3.22	3.44	K/W



10. Characteristics

Table 7. Char	acteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		40	43	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -40 °C		-	40.5	-	V

BUK9M15-40H

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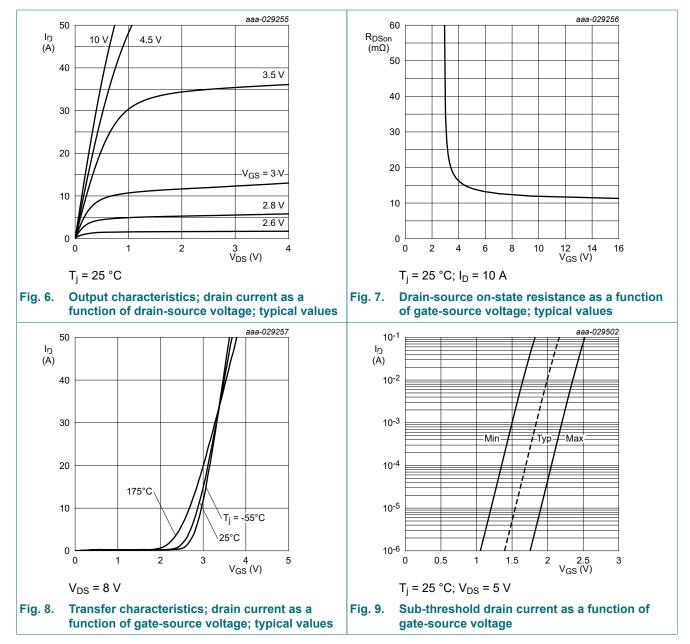
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u> ; Fig. 10	1.5	1.85	2.2	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 10</u>	-	-	2.6	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 10	0.7	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	0.24	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	17	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 11</u>	8.4	12.1	15	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 105 °C; <u>Fig. 12</u>	11.5	17.3	22.5	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 125 °C; <u>Fig. 12</u>	12.6	18.8	24.2	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 12	15.3	22.7	29.1	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; Fig. 11	10.6	15.3	19	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 105 °C; Fig. 12	14.5	21.7	28.5	mΩ
	V _{GS} = 4.5 V; I _D = 10 A; T _j = 125 °C; Fig. 12	16	23.4	30.6	mΩ	
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 175 °C; <u>Fig. 12</u>	19.4	28.1	36.9	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.3	0.9	2.3	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_{D} = 10 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 13; Fig. 14	-	11.6	16.2	nC
		I _D = 10 A; V _{DS} = 20 V; V _{GS} = 4.5 V;	-	5.3	7.4	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	2.2	3.3	nC
Q _{GD}	gate-drain charge		-	1.2	2.5	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	733	1026	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	247	346	pF
C _{rss}	reverse transfer capacitance		-	28	62	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	7.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	5.9	-	ns
t _{d(off)}	turn-off delay time] [-	8.1	-	ns
t _f	fall time		-	4.1	-	ns
Source-drai	n diode					
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ Fig. 17}$	-	19	-	ns
Q _r	recovered charge	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}$	-	11	-	nC

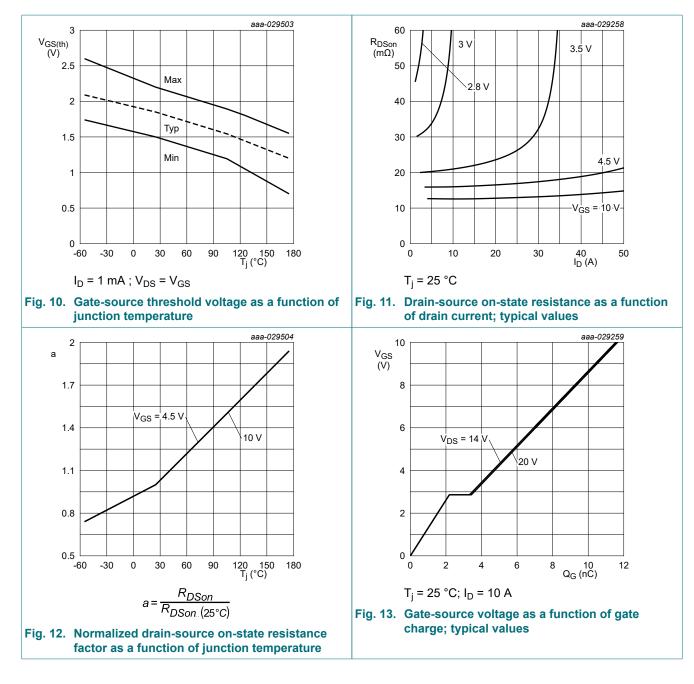
BUK9M15-40H

N-channel 40 V, 15.0 mΩ logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S	softness factor	$ I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{ V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 17} $	-	0.57	-	
		$ I_{S} = 10 \text{ A}; dI_{S}/dt = -500 A/\mu\text{s}; V_{GS} = 0 \text{V}; \\ V_{DS} = 20 \text{V}; \text{T}_{\text{j}} = 25 ^{\circ}\text{C}; \text{Fig. } 17 \\ $	-	0.36	-	

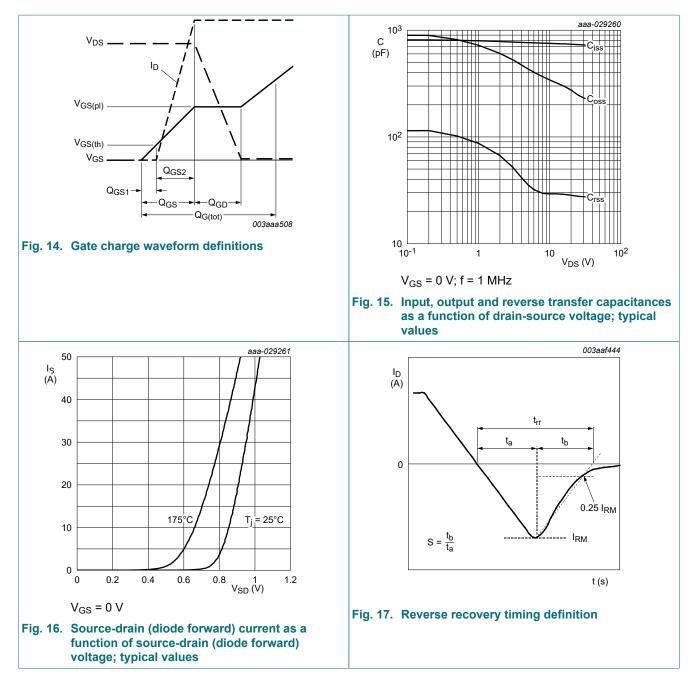


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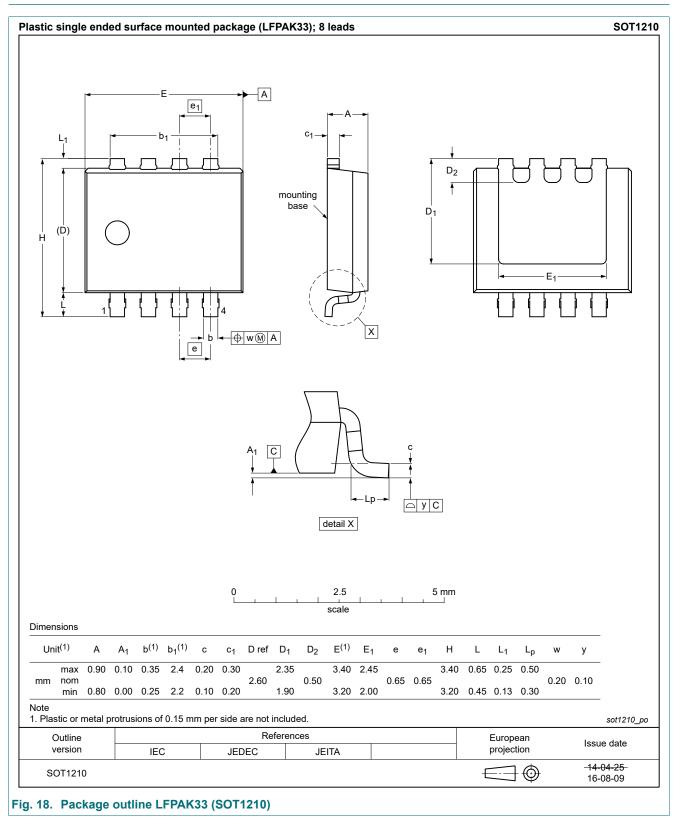
7 / 11

N-channel 40 V, 15.0 mΩ logic level MOSFET in LFPAK33



N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

11. Package outline



N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	4
10.	. Characteristics	4
11.	. Package outline	9
12.	. Legal information	10

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